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## PATENT ABSTRACTS OF JAPAN

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**H01L 21/265****H01L 21/205****H01L 21/324**(21) Application number: **59119932**(22) Date of filing: **13.06.84**(71) Applicant: **KOKUSAI ELECTRIC CO LTD**(72) Inventor: **HIURA KAZUO  
SUZUKI MASAYUKI**(54) **HEAT TREATING DEVICE OF SEMICONDUCTOR  
SUBSTRATE**

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(57) Abstract:

**PURPOSE:** To enable to be used for a wafer being circular by providing a plurality of projections for supporting a semiconductor substrate on a infrared ray or visible light beam transmitting disk levitated or rotated by gas injected from a gas nozzle of a base, thereby preventing the wafer from contaminating or cooling by the levitating gas.

**CONSTITUTION:** A wafer 1 is placed on a quartz fork 30 out of a quartz chamber 21, filled in the chamber 21, and placed on three quartz pins 29 of a quartz disk 28. When gas is supplied from a gas inlet 31 of a quartz base 22, the disk 28 is levitated and rotated by the gas injected from the nozzles 3, 3'. Many rod-shaped tungsten halogen lamps 26, 27 are fired to heat treat the wafer 1. Since the pins 29 are provided, the wafer 1 is prevented from contaminating or cooling due to the levitated gas, and can be used for the wafer not being circular.

